Wei-Kan Chu

List of Publications by Year
in descending order

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24
papers

331
citations

933447

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h-index

839539

18
g-index

24
all docs

24
docs citations

24
times ranked

237
citing authors

#	Article	IF	Citations
1	High thermal stability of vacancy clusters formed in MeV Si-self-ion-implanted Si. Applied Physics Letters, 2008, 93, 041908.	3.3	2
2	Diffusion of antimony in silicon in the presence of point defects. Nuclear Instruments & Methods in Physics Research B, 2007, 261, 1146-1149.	1.4	0
3	GaN nanorod assemblies on self-implanted (111) Si substrates. Microelectronic Engineering, 2006, 83, 1714-1717.	2.4	4
4	Effect of substrate temperature on the radiation damage from MeV Si implantation in Si. Nuclear Instruments & Methods in Physics Research B, 2006, 242, 434-436.	1.4	3
5	Application of high energy ion beam for the control of boron diffusion. Nuclear Instruments & Methods in Physics Research B, 2006, 242, 670-672.	1.4	0
6	The energy dependence of excessive vacancies created by high energy Si+ ion implantation in Si. Nuclear Instruments & Methods in Physics Research B, 2006, 242, 506-508.	1.4	0
7	Enhancement of boron solid solubility in Si by point-defect engineering. Applied Physics Letters, 2004, 84, 3325-3327.	3.3	19
8	Using point defect engineering to reduce the effects of energy nonmonochromaticity of B ion beams on shallow junction formation. Journal of Applied Physics, 2004, 96, 919-921.	2.5	4
9	Reduction of boride-enhanced diffusion by point defect engineering and its application for shallow junction formation. Nuclear Instruments & Methods in Physics Research B, 2003, 206, 413-416.	1.4	5
10	Boron diffusion in silicon: the anomalies and control by point defect engineering. Materials Science and Engineering Reports, 2003, 42, 65-114.	31.8	67
11	Application of High Energy Ion Beam on the Control of Boron Diffusion. Materials Research Society Symposia Proceedings, 2003, 792, 464.	0.1	0
12	Using point-defect engineering to increase stability of highly doped ultrashallow junctions formed by molecular-beam-epitaxy growth. Applied Physics Letters, 2003, 83, 2823-2825.	3.3	7
13	Stability of Ultrashallow Junction Formed by Low-Energy Boron Implant and Spike Annealing. Electrochemical and Solid-State Letters, 2003, 6, G82.	2.2	4
14	Athermal annealing at room temperature and enhanced activation of low- energy boron implants with high-energy Si coimplantation. Journal of Applied Physics, 2002, 92, 4307-4311.	2.5	16
15	Stability studies of ultrashallow junction formed by low energy boron implant and spike annealing. Journal of Applied Physics, 2002, 92, 5788-5792.	2.5	8
16	Reduction of boride enhanced diffusion in MeV-implanted silicon. Journal of Applied Physics, 2002, 92, 5793-5797.	2.5	12
17	Cluster-ion implantation: An approach to fabricate ultrashallow junctions in silicon. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 992.	1.6	22
18	Point Defect Engineering and Its Application in Shallow Junction Formation. Electrochemical and Solid-State Letters, 2002, 5, G93.	2.2	11

#	Article	IF	Citations
19	Retardation of boron diffusion in silicon by defect engineering. Applied Physics Letters, 2001, 78, 2321-2323.	3.3	41
20	Ultra-shallow Junction Formation via GeB- ion Implantation of Si. Materials Research Society Symposia Proceedings, 2000, 610, 451.	0.1	4
21	High-energy recoil implantation of boron into silicon. Applied Physics Letters, 2000, 76, 3953-3955.	3.3	20
22	Atmospheric-pressure chemical vapor deposition of fluorine-doped tin oxide thin films. Thin Solid Films, 1999, 345, 240-243.	1.8	40
23	Precursor Oxidation State Control of Film Stoichiometry in the Metalâˆ'Organic Chemical Vapor Deposition of Tin Oxide Thin Films. Chemistry of Materials, 1997, 9, 730-735.	6.7	30
24	Homoleptic Tin and Silicon Amido Compounds as Precursors for Low-Temperature Atmospheric Pressure Chemical Vapor Deposition of Tin and Silicon Oxide Thin Films. Chemistry of Materials, 1994, 6, 360-361.	6.7	12